

April 2008

PN2222A/MMBT2222A/PZT2222A NPN General Purpose Amplifier

- This device is for use as a medium power amplifier and switch requiring collector currents up to 500mA.
- · Sourced from process 19.



Absolute Maximum Ratings * Ta = 25 × C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V _{CEO}	Collector-Emitter Voltage	40	V	
V _{CBO}	Collector-Base Voltage	75	V	
V _{EBO}	Emitter-Base Voltage	6.0	V	
I _C	Collector Current	1.0	Α	
T _{STG}	Operating and Storage Junction Temperature Range	- 55 ~ 150	°C	

^{*}This ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

Thermal Characteristics T_a = 25°C unless otherwise noted

Symbol	Parameter	Max.			Units
		PN2222A	*MMBT2222A	**PZT2222A	UiillS
P _D	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	1,000 8.0	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3			°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	125	°C/W

^{*} Device mounted on FR-4 PCB 1.6" \times 1.6" \times 0.06".

¹⁾ These rating are based on a maximum junction temperature of 150 degrees C.

²⁾ These are steady limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

 $^{^{**}}$ Device mounted on FR-4 PCB 36mm \times 18mm \times 1.5mm; mounting pad for the collector lead min. 6cm².

Electrical Characteristics T_a = 25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Charac	teristics				
BV _{(BR)CEO}	Collector-Emitter Breakdown Voltage *	I _C = 10mA, I _B = 0	40		V
BV _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 10\mu A, I_E = 0$	75		V
BV _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10\mu A, I_C = 0$	6.0		V
I _{CEX}	Collector Cutoff Current	V _{CE} = 60V, V _{EB(off)} = 3.0V		10	nA
I _{CBO}	Collector Cutoff Current	V _{CB} = 60V, I _E = 0 V _{CB} = 60V, I _E = 0, T _a = 125°C		0.01 10	μ Α μ Α
I _{EBO}	Emitter Cutoff Current	V _{EB} = 3.0V, I _C = 0		10	nA
I _{BL}	Base Cutoff Current	V _{CE} = 60V, V _{EB(off)} = 3.0V		20	nA
On Charac	teristics				
h _{FE}	DC Current Gain	$\begin{split} & I_{C} = 0.1 \text{mA}, V_{CE} = 10 \text{V} \\ & I_{C} = 1.0 \text{mA}, V_{CE} = 10 \text{V} \\ & I_{C} = 10 \text{mA}, V_{CE} = 10 \text{V} \\ & I_{C} = 10 \text{mA}, V_{CE} = 10 \text{V}, T_{a} = -55^{\circ}\text{C} \\ & I_{C} = 150 \text{mA}, V_{CE} = 10 \text{V} * \\ & I_{C} = 150 \text{mA}, V_{CE} = 10 \text{V} * \\ & I_{C} = 500 \text{mA}, V_{CE} = 10 \text{V} * \end{split}$	35 50 75 35 100 50	300	
V _{CE(sat)}	Collector-Emitter Saturation Voltage *	I _C = 150mA, V _{CE} = 10V I _C = 500mA, V _{CE} = 10V		0.3 1.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage *	I _C = 150mA, V _{CE} = 10V I _C = 500mA, V _{CE} = 10V	0.6	1.2 2.0	V
Small Sign	al Characteristics				
f _T	Current Gain Bandwidth Product	I _C = 20mA, V _{CE} = 20V, f = 100MHz	300		MHz
C _{obo}	Output Capacitance	V _{CB} = 10V, I _E = 0, f = 1MHz		8.0	pF
C _{ibo}	Input Capacitance	V _{EB} = 0.5V, I _C = 0, f = 1MHz		25	pF
rb'C _c	Collector Base Time Constant	I _C = 20mA, V _{CB} = 20V, f = 31.8MHz		150	pS
NF	Noise Figure	I_C = 100μA, V_{CE} = 10V, R_S = 1.0KΩ, f = 1.0KHz		4.0	dB
Re(h _{ie})	Real Part of Common-Emitter High Frequency Input Impedance	I _C = 20mA, V _{CE} = 20V, f = 300MHz		60	Ω
Switching	Characteristics	· · · · · · · · · · · · · · · · · · ·		•	•
t _d	Delay Time	$V_{CC} = 30V, V_{EB(off)} = 0.5V,$		10	ns
t _r	Rise Time	I _C = 150mA, I _{B1} = 15mA		25	ns
t _s	Storage Time	V _{CC} = 30V, I _C = 150mA,		225	ns
t _f	Fall Time	I _{B1} = I _{B2} = 15mA		60	ns

^{*} Pulse Test: Pulse Width $\leq 300 \mu s,$ Duty Cycle $\leq 2.0\%$

Spice Model

NPN (Is = $14.34 \, \text{f} \, \text{Xti} = 3 \, \text{Eg} = 1.11 \, \text{Vaf} = 74.03 \, \text{Bf} = 255.9 \, \text{Ne} = 1.307 \, \text{Ise} = 14.34 \, \text{Ikf} = .2847 \, \text{Xtb} = 1.5 \, \text{Br} = 6.092 \, \text{Isc} = 0 \, \text{Ikr} = 0 \, \text{Rc} = 1 \, \text{Cjc} = 7.306 \, \text{Mjc} = .3416 \, \text{Vjc} = .75 \, \text{Fc} = .5 \, \text{Cje} = 22.01 \, \text{p} \, \text{Mje} = .377 \, \text{Vje} = .75 \, \text{Tr} = 46.91 \, \text{n} \, \text{Tf} = 411.1 \, \text{p} \, \text{Itf} = .6 \, \text{Vtf} = 1.7 \, \text{Xtf} = 3 \, \text{Rb} = 10)$

Typical Characteristics

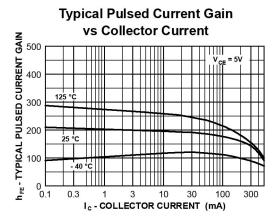


Figure 1. Typical Pulsed Current Gain vs Collector Current

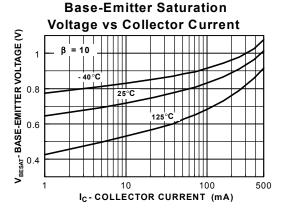


Figure 3. Base-Emitter Saturation Voltage vs Collector Current

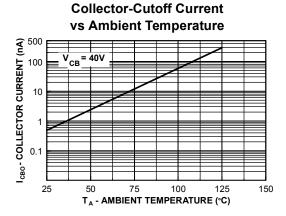


Figure 5. Collector Cutoff Current vs Ambient Temperature

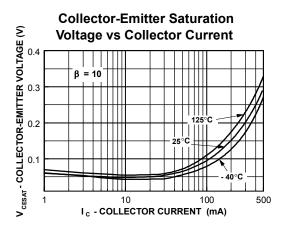


Figure 2. Collector-Emitter Saturation Voltage vs Collector Current

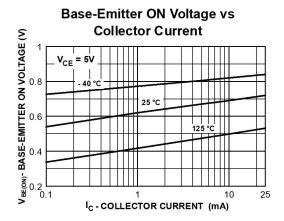


Figure 4. Base-Emitter On Voltage vs Collector Current

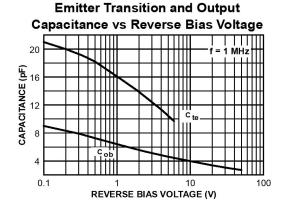


Figure 6. Emitter Transition and Output Capacitance vs Reverse Bias Voltage

Typical Characteristics

Turn On and Turn Off Times vs Collector Current

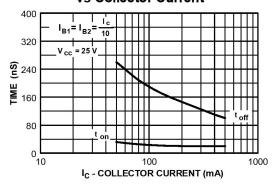


Figure 1. Turn On and Turn Off Times vs Collector Current

Power Dissipation vs Ambient Temperature

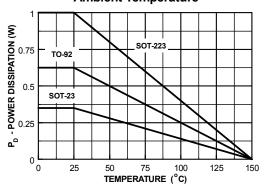


Figure 3. Power Dissipation vs **Ambient Temperature**

Common Emitter Characteristics

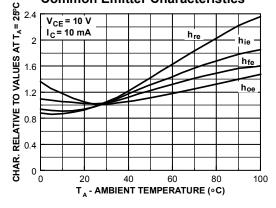


Figure 5. Common Emitter Characteristics

Switching Times vs Collector Current

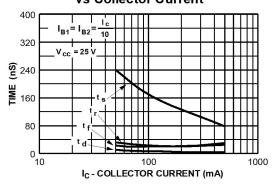


Figure 2. Switching Times vs Collector Current

Common Emitter Characteristics

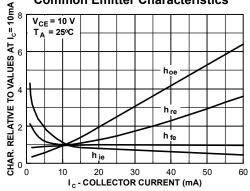


Figure 4. Common Emitter Characteristics

Common Emitter Characteristics

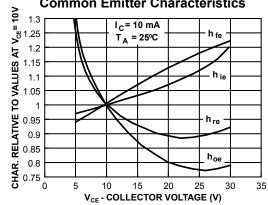


Figure 6. Common Emitter Characteristics





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